



# **CERTIFICATE**

## N°CC0092-20140508

## **Applicant**

### **TOPSUN**

B-101,GIDC,Electronic Estate,Sec-25 Gandhinagar - 382028 Gujarat - INDIA

## **Factory**

#### **TOPSUN**

R S No. 892, Near 66KV GEB substation Jagudan Cross Road, At & PO-Linch, Ta & Dist- Mehsana 384435 Gujarat - INDIA

## **Module type**

TEL72PXXX; XXX=260 to 320W each step of 5W TEL60PXXX; XXX=215 to 265W each step of 5W TEL54PXXX; XXX=200 to 240W each step of 5W TEL48PXXX; XXX=160 to 200W each step of 5W

## Test report: 20140508-001 (BOM 1), 20140508-001 (BOM 2)

In consideration of the test results in the above mentioned report, no potential-induced degradation of the tested modules samples have been detected: no degradation of the power output and no default added on EL images.

## References



IEC TS 62804-1: 2015

Photovoltaic (PV) modules - Test methods for the detection of potential-induced degradation - Part 1: Crystalline silicon

## **Conditions**

Date: 28/09/2015

Test method (a) of IEC TS 62804-1: Module temperature: 60°C; Chamber relative humidity: 85%; Test duration: 96h; Voltage module rated system: 1000V Only one polarity tested: Connection (negative bias – Positively grounded) – Only one sample tested on each BOM.

Each modification of design, material or component is not covered by this type approval. Each modification requires evaluation by a qualifying test laboratory. This certificate is only valid for the samples tested and for the tests described in the report mentioned above. It does not imply that a control or supervision of the production process have been done by CERTISOLIS

Jérôme BECCAVIN, CEO

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